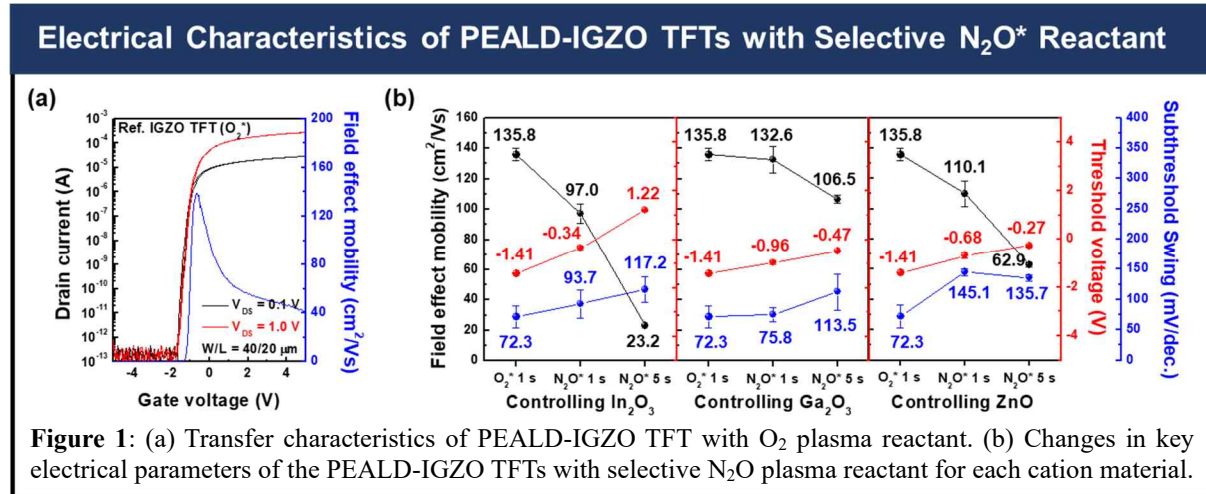


Supplemental Document

Figure 1 (a) shows the transfer characteristic of PEALD-IGZO TFT with O₂ plasma reactant. To gain insight into N dopants for each cation of PEALD-IGZO TFTs, an N₂O plasma reactant was selectively applied for each PEALD cation cycle during IGZO deposition. **Figure 1 (b)** illustrates the variations of key electrical parameters of the PEALD-IGZO TFTs with selective N₂O plasma reactant.



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